

MDL-NS-660/1-180mW



**NANOSECOND PULSED RED
DIODE LASER AT 660nm**

This series laser products with excellent material removal rate, are widely used in microelectronics, material processing, solar energy and medical equipment manufacturing, etc.

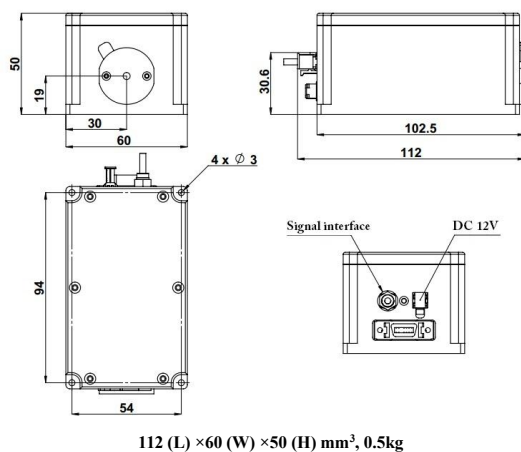


SPECIFICATIONS

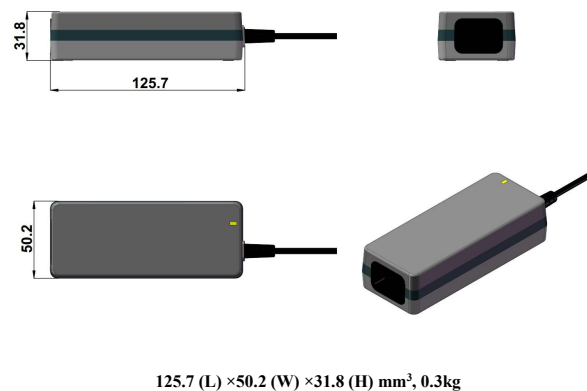
Central wavelength (nm)	660±5	
Operating mode	Pulsed	
Peak power (mW) ¹	1-100	100-180
Power stability (rms, 4 hours ± 3°C)	<2%, <1%, <0.5%	
Pulse width (FWHM)	10ns-10ms	15ns-10ms
Transverse mode	Near TEM ₀₀	
M ²	<1.2	
Beam diameter at the aperture (1/e ² ,mm)	~1.2	
Beam divergence, full angle (mrad)	<1.0	
Polarization ratio	>50:1, (>100:1 optional) Horizontal±5 degree (Vertical optional)	
Rep. rate ²	DC-30MHz	DC-30MHz
Rise Time (ns)	<4	<10
Fall Time (ns)	<3	<3
Modulation Depth (extinction ratio)	>1000000:1	
Warm-up time (minutes)	<5	
Cooled method	Conduction	
Beam height from base plate (mm)	19	
Operating temperature (°C)	10-35	
Operating voltage (VDC)	12V/3.34A	
Expected lifetime (hours)	>10000	



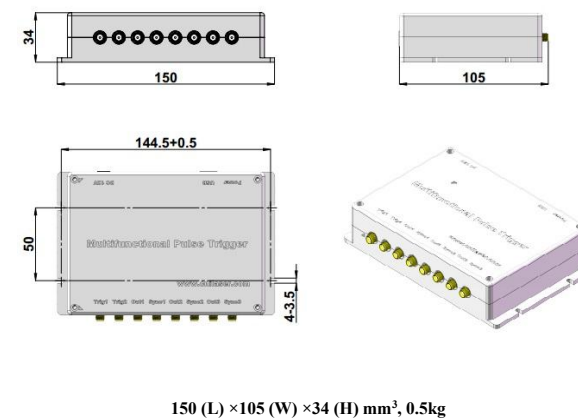
LASER HEAD (DRIVER Integrated)³



POWER SUPPLY (100-240VAC) optional



MULTIFUNCTIONAL PULSE TRIGGER optional



1 Any power level can be selected in this range.

2 Both internal and external triggers are acceptable. The internal trigger supports a frequency range of DC-25MHz.

3 RS232 control optional, output power adjustable 10-100% by software.

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